

FCB36N60N

N-Channel SupreMOS® MOSFET

600 V, 36 A, 90 mΩ

Features

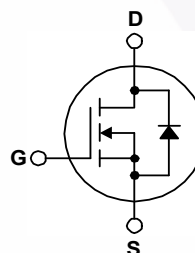
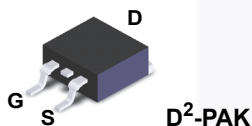
- $R_{DS(on)} = 81 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 18 \text{ A}$
- Ultra Low Gate Charge (Typ. $Q_g = 86 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 361 \text{ pF}$)
- 100% Avalanche Tested
- RoHS Compliant

Applications

- Solar Inverter
- AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest R_{sp} on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCB36N60N	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	± 30	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	A
		- Continuous ($T_C = 100^\circ\text{C}$)	
I_{DM}	Drain Current	- Pulsed (Note 1)	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	mJ
I_{AR}	Avalanche Current	(Note 1)	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt	(Note 3)	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	W
		- Derate Above 25°C	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FCB36N60N	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (1 in ² Pad of 2-oz Copper), Max.	40	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCB36N60N	FCB36N60N	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$, $T_C = 25^\circ\text{C}$	600	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to 25°C	-	0.7	-	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 480\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	10	μA
		$V_{DS} = 480\text{ V}$, $V_{GS} = 0\text{ V}$, $T_C = 125^\circ\text{C}$	-	-	100	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{ V}$, $V_{DS} = 0\text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 18\text{ A}$	-	81	90	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}$, $I_D = 18\text{ A}$	-	41	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	-	3595	4785	pF
C_{oss}	Output Capacitance		-	149	200	pF
C_{rss}	Reverse Transfer Capacitance		-	4	6	pF
C_{oss}	Output Capacitance	$V_{DS} = 380\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	-	80	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V}$ to 380 V , $V_{GS} = 0\text{ V}$	-	361	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}$, $I_D = 18\text{ A}$, $V_{GS} = 10\text{ V}$ (Note 4)	-	86	112	nC
Q_{gs}	Gate to Source Gate Charge		-	15.4	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	26.4	-	nC
ESR	Equivalent Series Resistance (G-S)	$f = 1\text{ MHz}$	-	1	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}$, $I_D = 18\text{ A}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$ (Note 4)	-	23	56	ns
t_r	Turn-On Rise Time		-	22	54	ns
$t_{d(off)}$	Turn-Off Delay Time		-	94	198	ns
t_f	Turn-Off Fall Time		-	4	18	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	36	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	108	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 18 A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 18 A, dI _F /dt = 100 A/μs	-	574	-	ns
Q _{rr}	Reverse Recovery Charge		-	10	-	μC

Notes:

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. $I_{AS} = 12\text{ A}$, $R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 36\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} = 380\text{ V}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

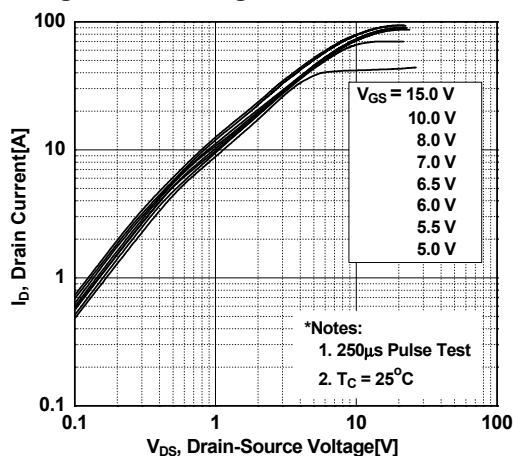


Figure 2. Transfer Characteristics

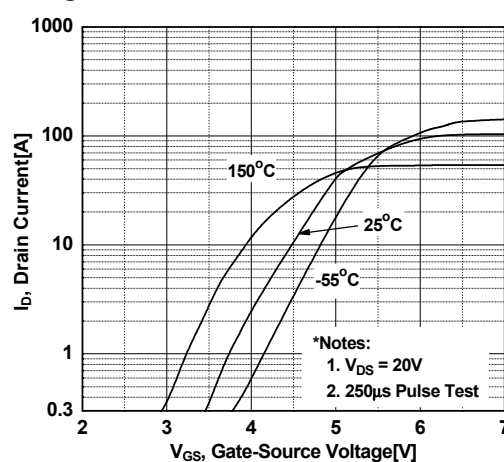


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

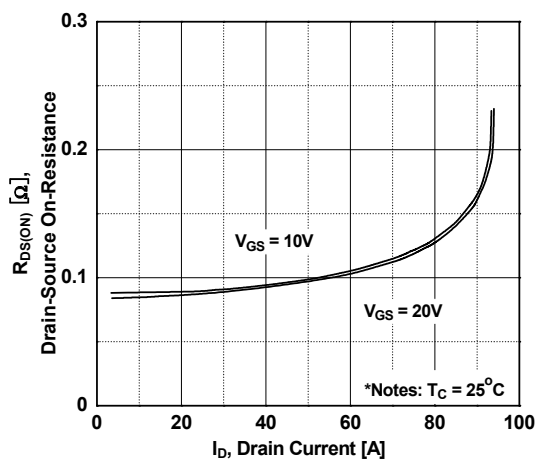


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

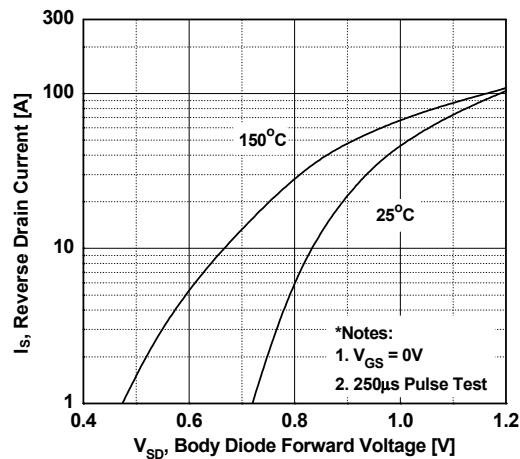


Figure 5. Capacitance Characteristics

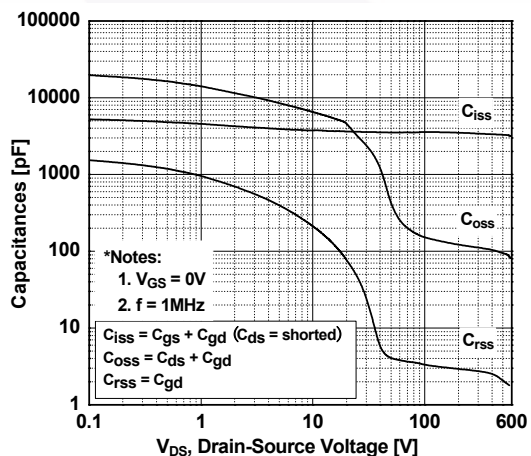
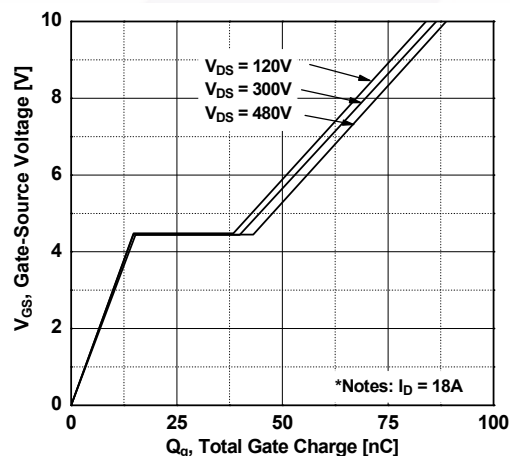


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

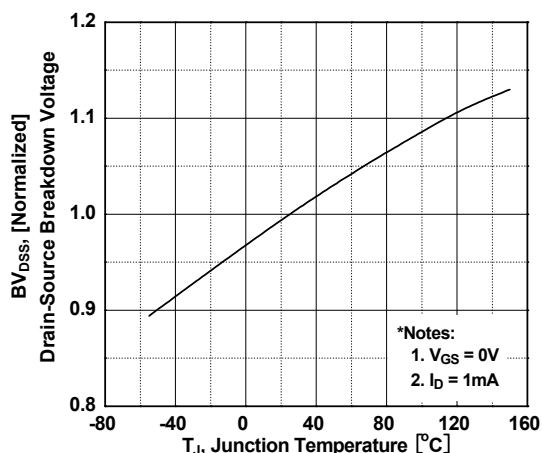


Figure 8. On-Resistance Variation vs. Temperature

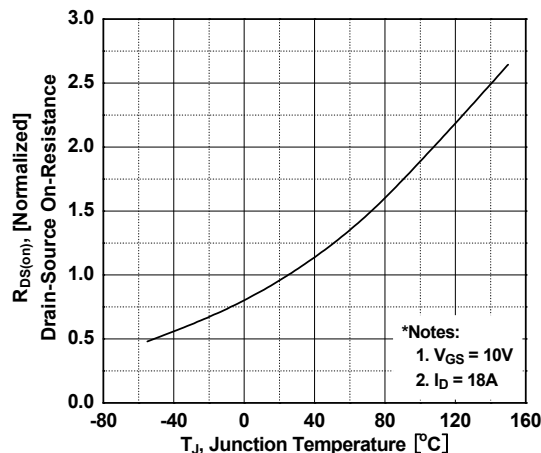


Figure 9. Maximum Safe Operating Area

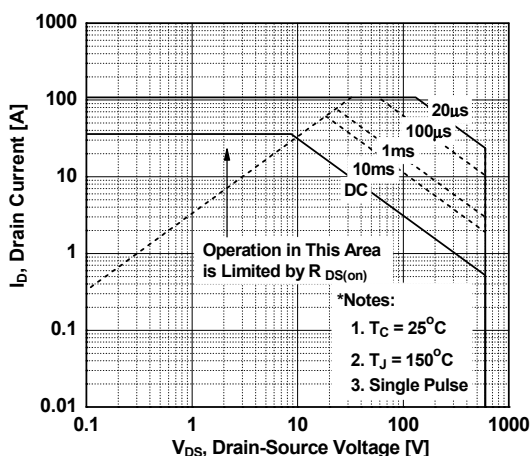


Figure 10. Maximum Drain Current vs. Case Temperature

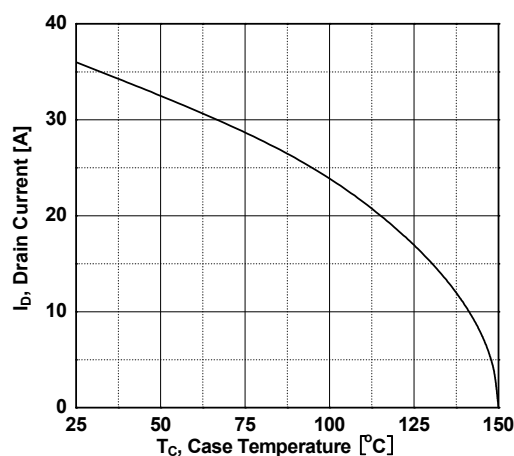


Figure 11. Transient Thermal Response Curve

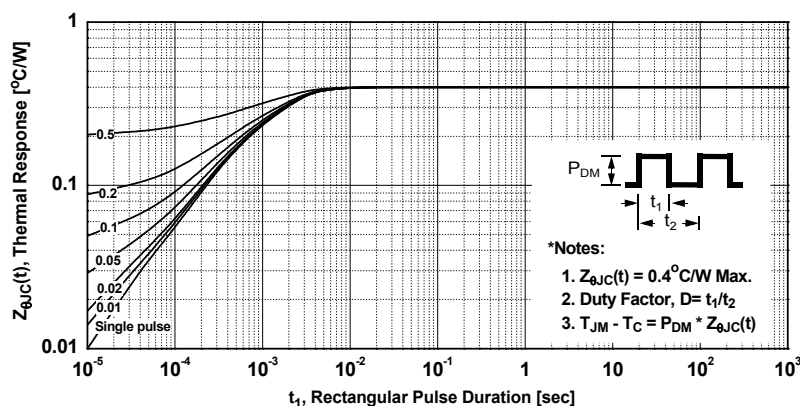




Figure 12. Gate Charge Test Circuit & Waveform

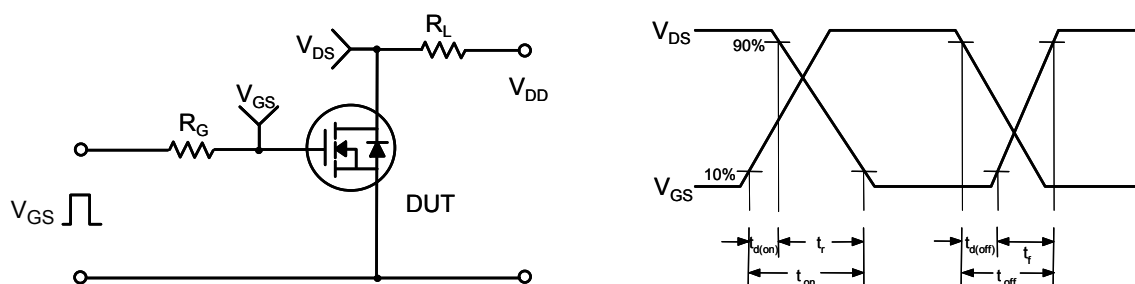


Figure 13. Resistive Switching Test Circuit & Waveforms

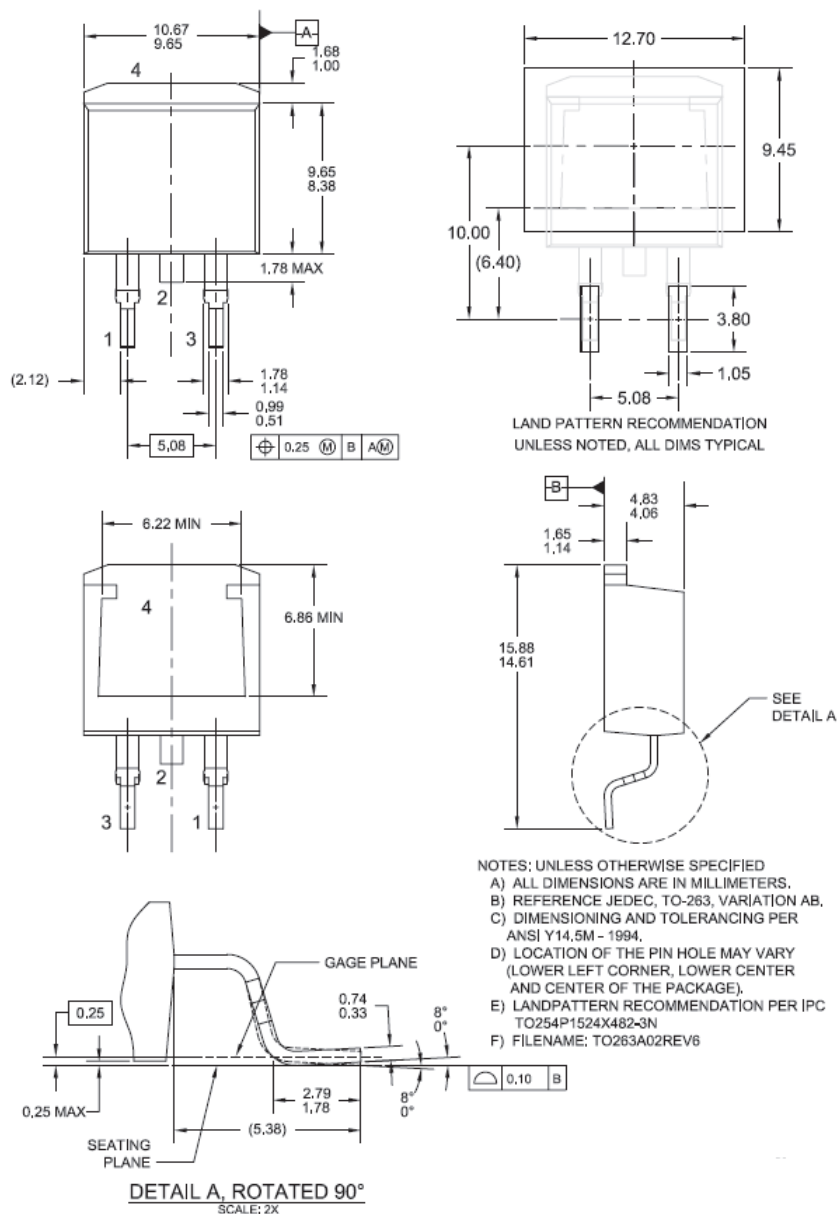


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

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